



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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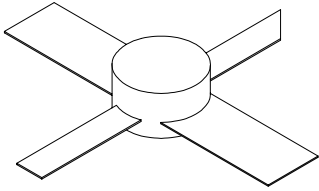
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1035MP

**35 Watts, 50 Volts
Avionics 1025 - 1150 MHz**

GENERAL DESCRIPTION The 1035 MP is a COMMON BASE bipolar transistor. It is designed for pulsed systems in the frequency band 1025-1150 MHz. The device has gold thin-film metallization for proven highest MTTF. The transistor includes input prematch for broadband capability. Low thermal resistance package reduces junction temperature, extends life.	CASE OUTLINE 55FW-1
ABSOLUTE MAXIMUM RATINGS Maximum Power Dissipation @ 25°C ² 125 Watts Pk Maximum Voltage and Current BVces Collector to Emitter Voltage 65 Volts BVebo Emitter to Base Voltage 3.5 Volts Ic Collector Current 2.5 Amps Pk Maximum Temperatures Storage Temperature - 65 to + 150°C Operating Junction Temperature + 200°C	

ELECTRICAL CHARACTERISTICS @ 25°C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
P _{OUT}	Power Out	F = 1025-1150 MHz	35			W
P _{IN}	Power Input	V _{cc} = 50 Volts			3.5	W
P _G	Power Gain	PW = 10 μsec, DF = 1%	10	10.5		dB
η _c	Efficiency			45		%
VSWR	Load Mismatch Tolerance	F = 1090 MHz			10:1	

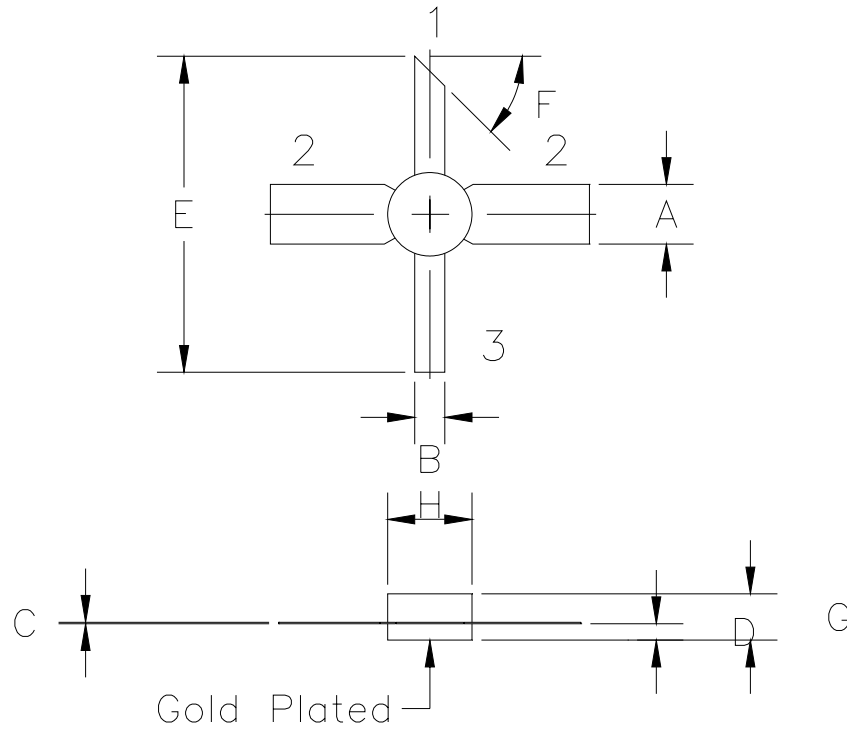
FUNCTIONAL CHARACTERISTICS @ 25°C

BVebo	Emitter to Base Breakdown	I _e = 5 mA	3.5			V
BVces	Collector to Emitter Breakdown	I _c = 15mA	65			V
H _{fe}	DC Current Gain	V _{ce} = 5V, I _c = 100 mA	20			
Cob	Output Capacitance	V _{cb} = 50 V, f = 1 MHz		17	20	pF
θ _{jc} ²	Thermal Resistance				1.4	°C/W

Note 1: At rated output power and pulse conditions
 2: At rated pulse conditions

Issue December 6, 1995

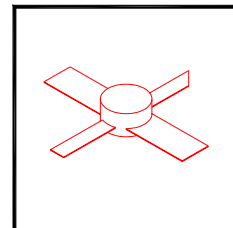
1035MP



STYLE 1:
 PIN1 = COLLECTOR
 2 = BASE (2X)
 3 = EMITTER

STYLE 2:
 PIN1 = COLLECTOR
 2 = EMITTER (2X)
 3 = BASE

DIM	MILLIMETER	±TOL	INCHES	±TOL
A	5.08	.13	.200	.005
B	7.11 DIA	.13	.280 DIA	.005
C	0.13	.02	.005	.001
D	1.40	.13	.055	.005
E	26.92	.64	1.060	.025
F	45°	5°	45°	5°
G	3.94	REF	.155	REF
H	2.54	.13	.100	.005



GHz TECHNOLOGY
 RF - MICROWAVE SILICON POWER TRANSISTORS

DWG NO.

55FW